



MOLD TYPE BIPOLAR TRANSISTORS

Ratings and Specifications

10 General use transistors

- Can be available to general applications
- Designed for complementary use

Device type	V _{CB0}	V _{CE0}	V _{CE0}	I _c	P _c	h _{FE}			Switching time (Max.)			Package	Net mass Grams	Equivalent circuit Page 31
	Volts	Volts	(sus) Volts	cont. Amps.	Watts	min.	I _c	V _{CE}	t _{on}	t _{stg}	t _r			
							Amps.	Volts	μsec.	μsec.	μsec.			
2SD847	40	40	40	15	100	40	5	5	—	—	—	TO-3P	6	—
2SB757	-40	-40	-40	-15	100	40	-5	-5	—	—	—	TO-3P	6	—
2SD1117	40	40	40	10	50	40	2	5	—	—	—	TO-220AB	2	—
2SB850	-40	-40	-40	-10	50	40	-2	-5	—	—	—	TO-220AB	2	—
2SB1532	-40	-40	-40	-10	40	40	-2	-5	—	—	—	TO-220F17	2.5	—
2SB862	-120	-80	-80	-5	30	1000	-1	-5	—	—	—	TO-220AB	2	—
ET367	-120	-80	-80	-5	30	1000	-1	-5	—	—	—	TO-220F17	2.5	Fig. B1
2SD1157	80	50	50	4	25	250	0.5	5	0.5	3.0	0.8	TO-220AB	2	—

11 Building block transistors

- Suitable for motor control applications
- High voltage, high current capacity
- V_{CE0}: 300 – 600V, I_c: 100 – 500A
- Easily connected in parallel and control currents up to 1200A

Device type	V _{CB0}	V _{CE0}	V _{CE0}	I _c	P _c	h _{FE}			Switching time (Max.)			Package	Net mass Grams	Equivalent circuit Page 31
	Volts	Volts	(sus) Volts	cont. Amps.	Watts	min.	I _c	V _{CE}	t _{on}	t _{stg}	t _r			
							Amps.	Volts	μsec.	μsec.	μsec.			
1D200A-020	300	300	250	200	800	100	200	5	2.0	12	3.0	BBT II	145	Fig. B6
1D500A-030	400	400	300	500	2000	500	500	2	2.0	12	4	BBT IV	365	Fig. B11
ET188	400	400	300	100	600	200	100	5	2.0	12.0	3.0	BBT II	145	Fig. B3
ETN35-030	400	400	300	300	1500	150	300	5	2.0	12.0	1.2	BBT III	270	—
ETM36-030	400	400	320	200	1000	150	200	5	2.0	10.0	1.2	BBT III	270	Fig. B4
ETN36-030	400	400	320	300	1500	150	300	5	2.0	10.0	1.2	BBT III	270	Fig. B4
ET127	600	600	450	100	770	100	100	5	4.0	10.0	3.0	BBT I	200	Fig. B9
ETN01-055	600	600	550	200	1500	8	120	5	2.0	8.0	2.0	BBT III	270	Fig. A1
ETN31-055	600	600	550	200	1500	70	200	5	2.0	12.0	3.0	BBT III	270	Fig. B9